STD105N10F7AG

Automotive-grade N-channel 100 V, 6.8 mΩ typ., 80 A, STripFET™ F7 Power MOSFET in a DPAK package

Datasheet - production data

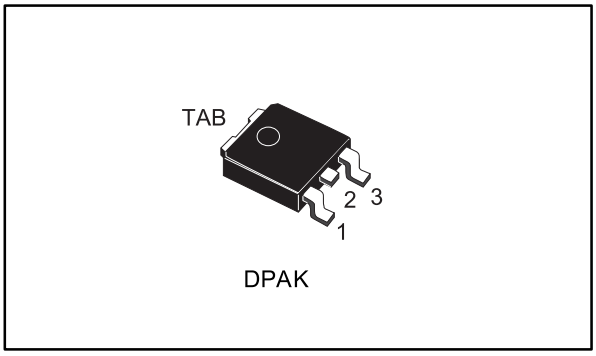
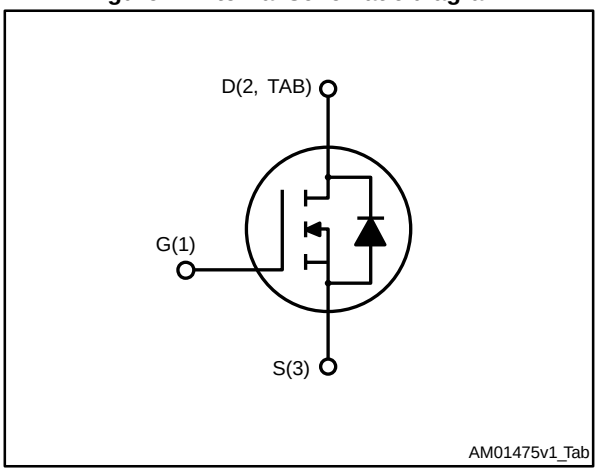


Figure 1: Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D	P_{TOT}
STD105N10F7AG	100 V	8 mΩ	80 A	120 W

- Designed for automotive applications and AEC-Q101 qualified
- Among the lowest $R_{DS(on)}$ on the market
- Excellent FoM (figure of merit)
- Low C_{rss}/C_{iss} ratio for EMI immunity
- High avalanche ruggedness

Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Table 1: Device summary

Order code	Marking	Package	Packing
STD105N10F7AG	105N10F7	DPAK	Tape and reel

Contents

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at T_C = 25 °C	80	A
I_D	Drain current (continuous) at T_C = 100 °C	62	A
I_{DM}(1)	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at T_C = 25 °C	120	W
T_{stg}	Storage temperature range	-55 to 175	°C
T_J	Operation junction temperature range		

Notes:

(1)Pulse width limited by safe operating area.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	1.25	°C/W
$R_{thj\text{-}pcb}$(1)	Thermal resistance junction-pcb	50	

Notes:

(1)When mounted on FR-4 board of 1 inch², 2oz Cu.

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
E_{AS}	Single pulse avalanche energy T_J = 25 °C, L = 3.5 mH, I_{AS} = 15 A, V_{DD} = 50 V, V_{GS} = 10 V	400	mJ

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 5: On/Off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage (V_{GS} = 0)	I_D = 250 µA	100			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = 100 V			1	µA
		V_{DS} = 100 V, T_C = 125 °C (1)			100	µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{GS} = ± 20 V			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS} , I_D = 250 µA	2.5		4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D= 40 A		6.8	8	mΩ

Notes:

(1)Defined by design, not subject to production test.

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 50 V, f = 1 MHz, V_{GS} = 0 V	-	4369	-	pF
C_{oss}	Output capacitance		-	823	-	pF
C_{rss}	Reverse transfer capacitance		-	36	-	pF
Q_g	Total gate charge	V_{DD} = 50 V, I_D = 80 A, V_{GS} = 10 V (see *Figure 14: "Test circuit for gate charge behavior"*)	-	61	-	nC
Q_{gs}	Gate-source charge		-	26	-	nC
Q_{gd}	Gate-drain charge		-	13	-	nC

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 50 V, I_D = 40 A, R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 13: "Test circuit for resistive load switching times"* and *Figure 18: "Switching time waveform"*)	-	27	-	ns
t_r	Rise time		-	40	-	ns
$t_{d(off)}$	Turn-off delay time		-	46	-	ns
t_f	Fall time		-	15	-	ns

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		80	A
I_{SDM}(1)	Source-drain current (pulsed)		-		320	A
V_{SD}(2)	Forward on voltage	I_{SD} = 80 A, V_{GS} = 0 V	-		1.2	V
t_{rr}	Reverse recovery time	I_{SD} = 80 A, di/dt = 100 A/µs V_{DD} = 80 V, T_j = 150 °C	-	77		ns
Q_{rr}	Reverse recovery charge		-	146		nC
I_{RRM}	Reverse recovery current		-	4		A

Notes:

(1)Pulse width limited by safe operating area.

(2)Pulsed: pulse duration = 300 µs, duty cycle 1.5 %.

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

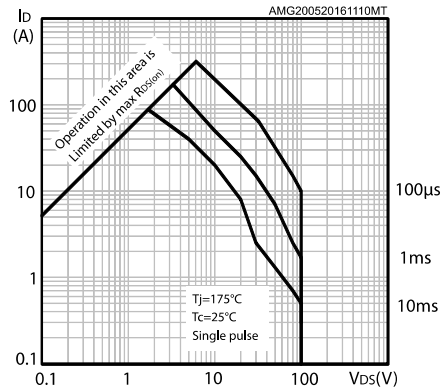


Figure 3: Thermal impedance

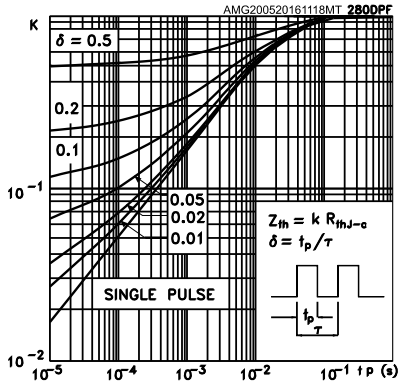


Figure 4: Output characteristics

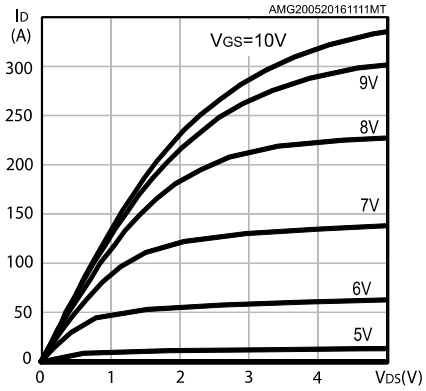


Figure 5: Transfer characteristics

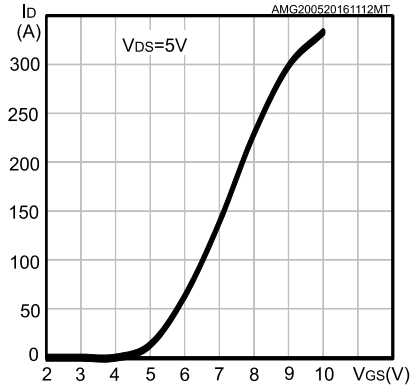


Figure 6: Normalized $V_{(BR)DSS}$ vs temperature

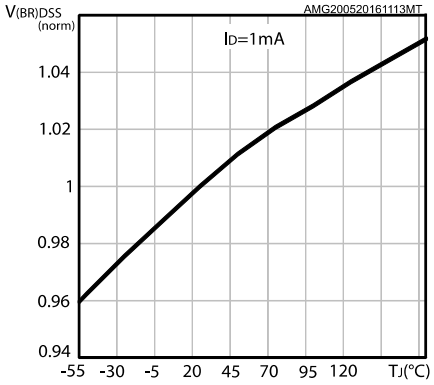


Figure 7: Static drain-source on-resistance

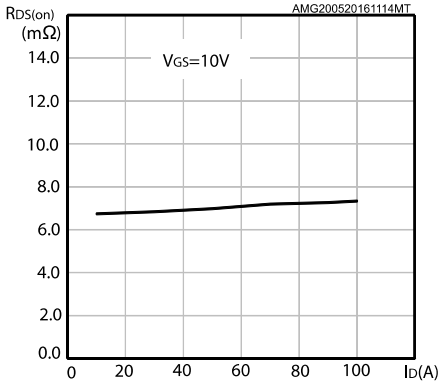


Figure 8: Gate charge vs gate-source voltage

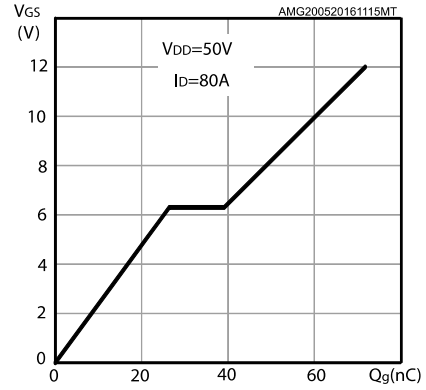


Figure 9: Capacitance variations

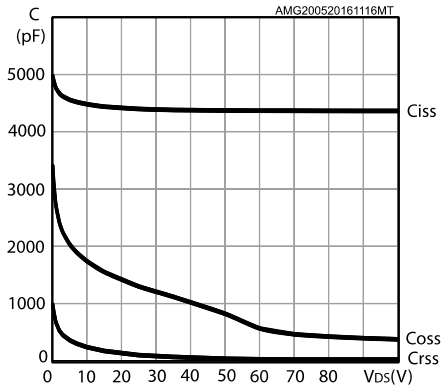


Figure 10: Normalized gate threshold voltage vs temperature

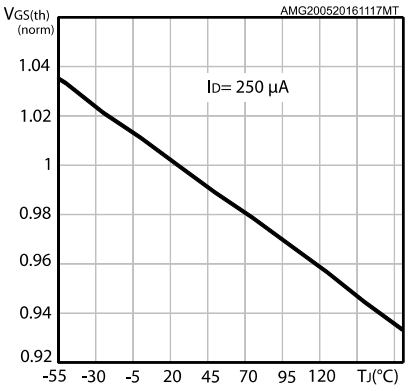


Figure 11: Normalized on-resistance vs temperature

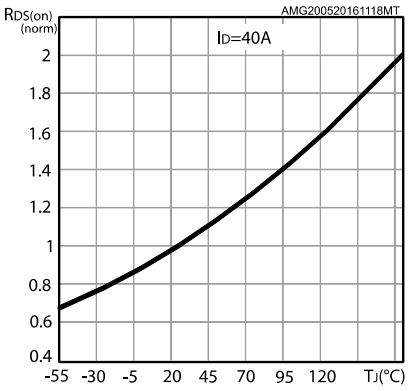
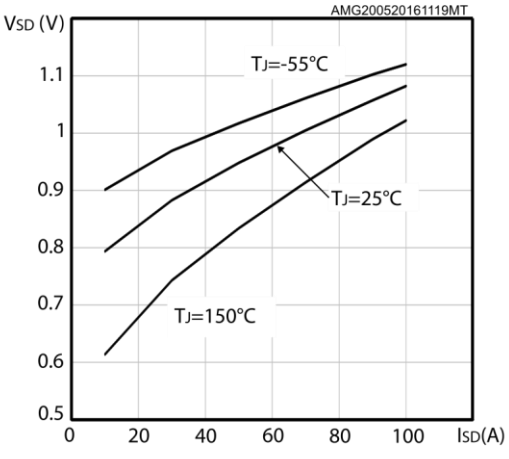


Figure 12: Source-drain diode forward characteristics



3 Test circuits

Figure 13: Test circuit for resistive load switching times

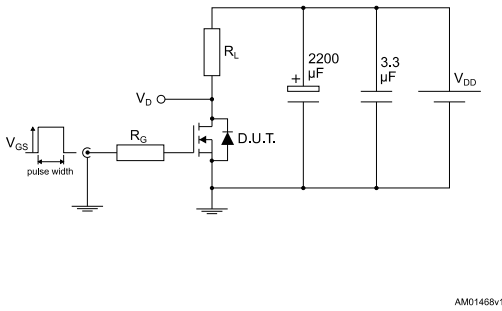


Figure 14: Test circuit for gate charge behavior

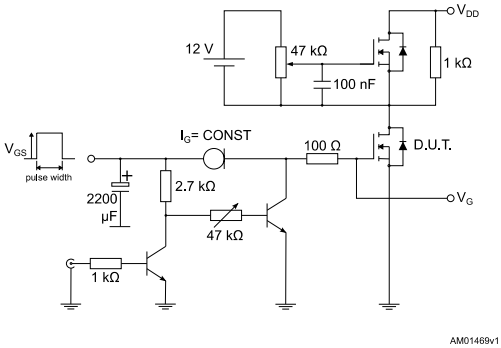


Figure 15: Test circuit for inductive load switching and diode recovery times

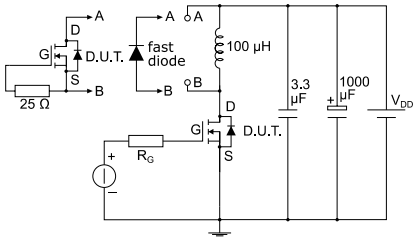


Figure 16: Unclamped inductive load test circuit

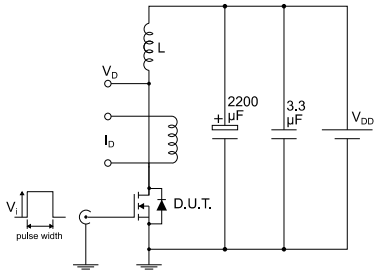


Figure 17: Unclamped inductive waveform

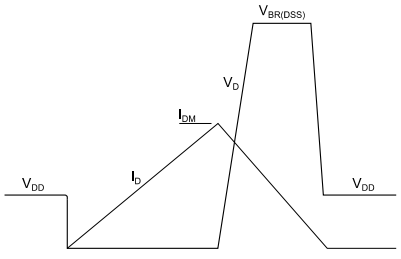
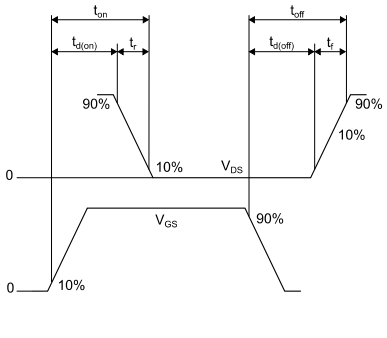


Figure 18: Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

4.1 DPAK (TO-252) type A2 package information

Figure 19: DPAK (TO-252) type A2 package outline

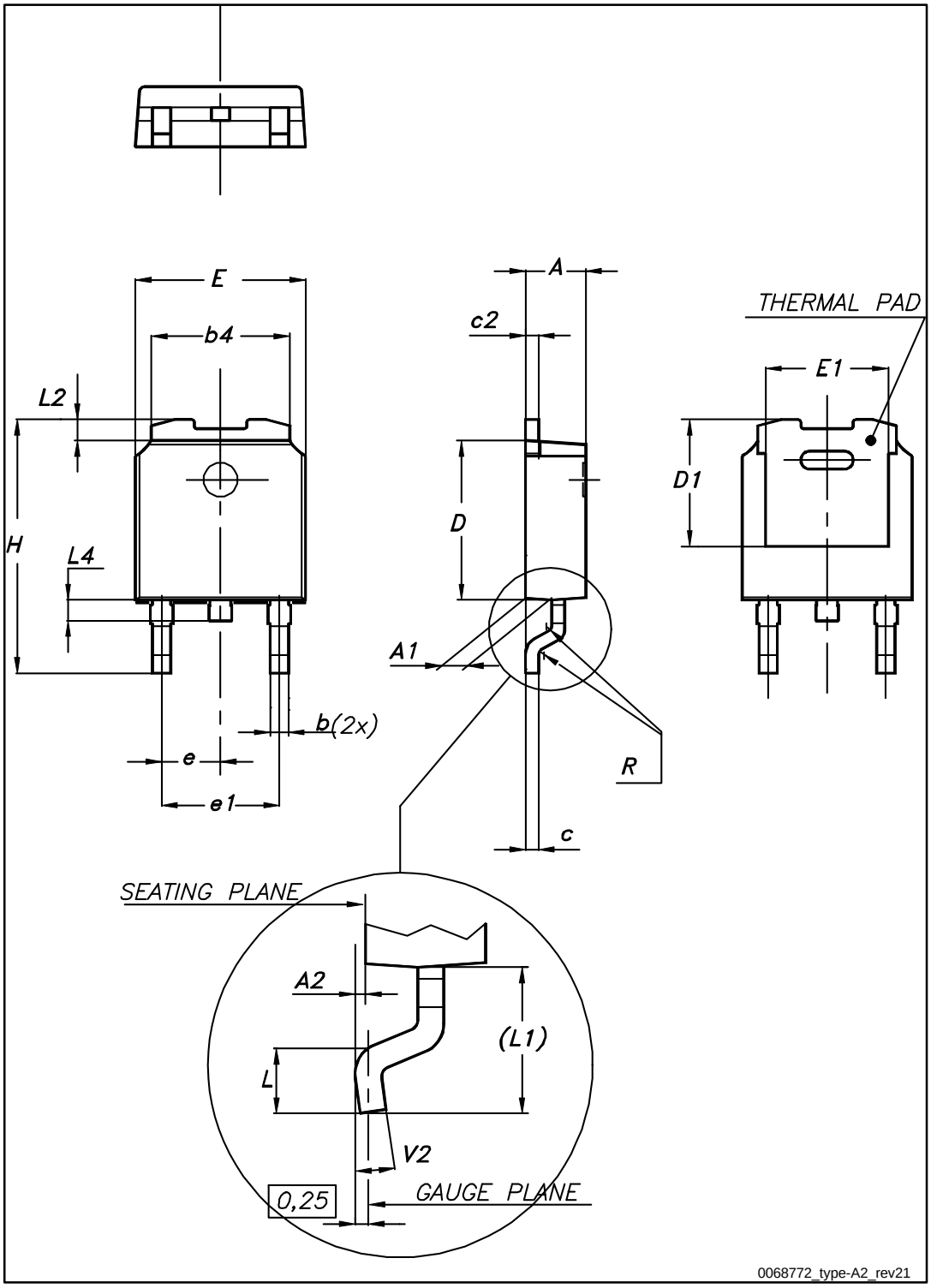
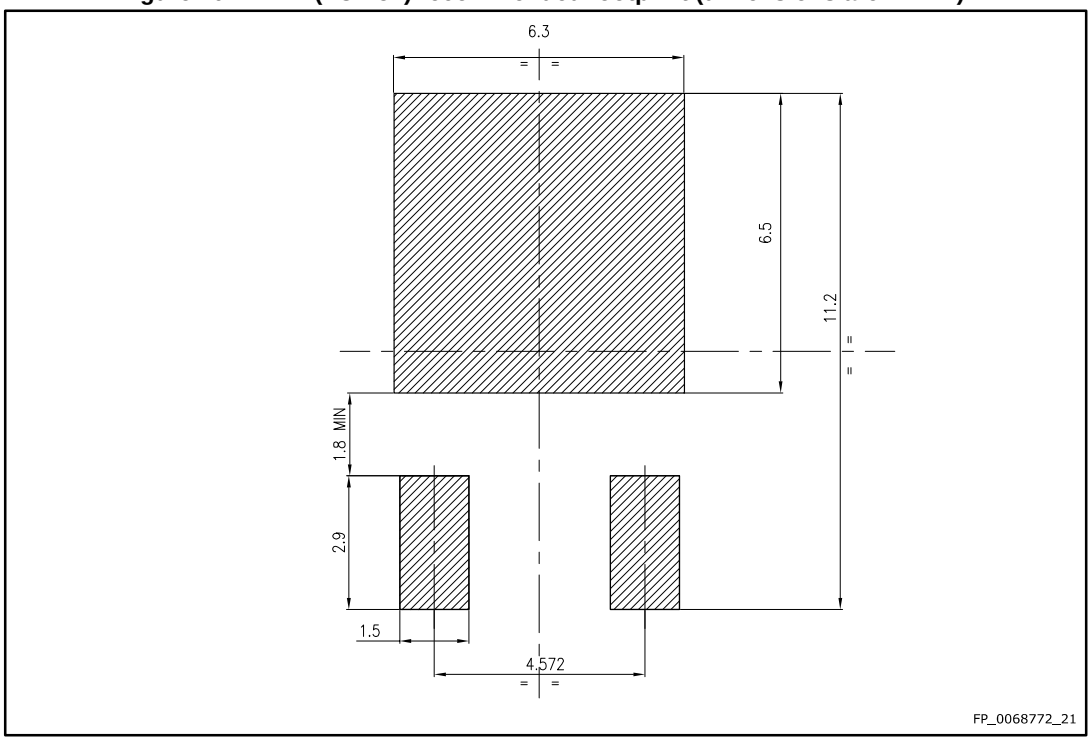


Table 9: DPAK (TO-252) type A2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.16	2.28	2.40
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

Figure 20: DPAK (TO-252) recommended footprint (dimensions are in mm)



5 Revision history

Table 10: Document revision history

Date	Revision	Changes
23-Oct-2014	1	First release.
30-Oct-2014	2	Document status promoted from preliminary to production data.
20-May-2016	3	Updated Section 4.1: "DPAK (TO-252) type A2 package information". Minor text changes.
03-Jun-2016	4	Updated title and features in cover page. Updated *Table 5: "On/Off states"*. Minor text changes.

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